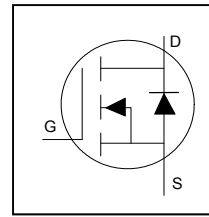


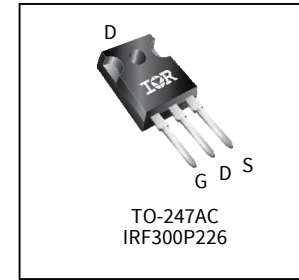
IR MOSFET - StrongIRFET™



| | |
|--------------------------------|-------------|
| V_{DSS} | 300V |
| R_{DS(on)} typ. | 16mΩ |
| | max |
| I_D | 75A |

Applications

- UPS and Inverter applications
- Half-bridge and full-bridge topologies
- Resonant mode power supplies
- DC/DC and AC/DC converters
- OR-ing and redundant power switches
- Brushed and BLDC Motor drive applications
- Battery powered circuits



Benefits

- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dv/dt and di/dt Capability
- Pb-Free ; RoHS Compliant ; Halogen-Free



Halogen-Free



RoHS

| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

| Base part number | Package Type | Standard Pack | | Orderable Part Number |
|------------------|--------------|---------------|----------|-----------------------|
| | | Form | Quantity | |
| IRF300P226 | TO-247AC | Tube | 25 | IRF300P226 |

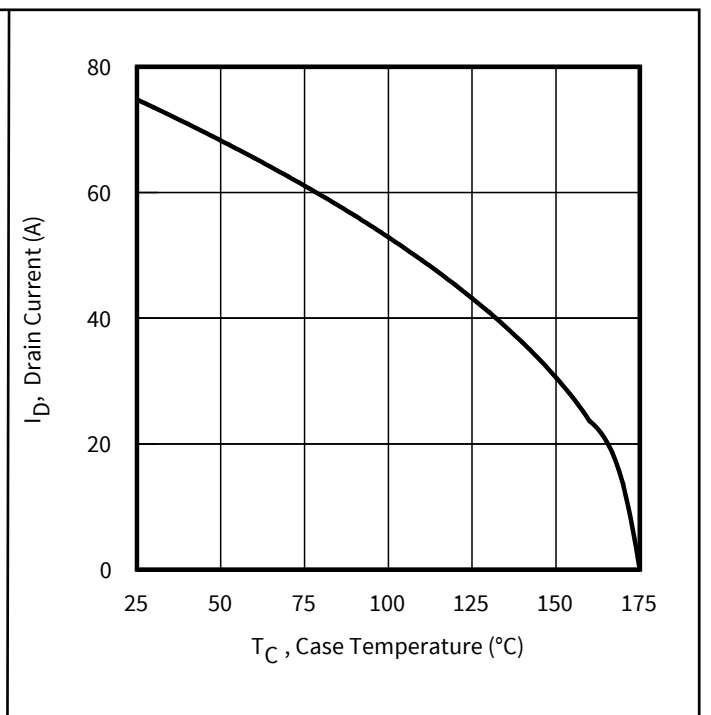
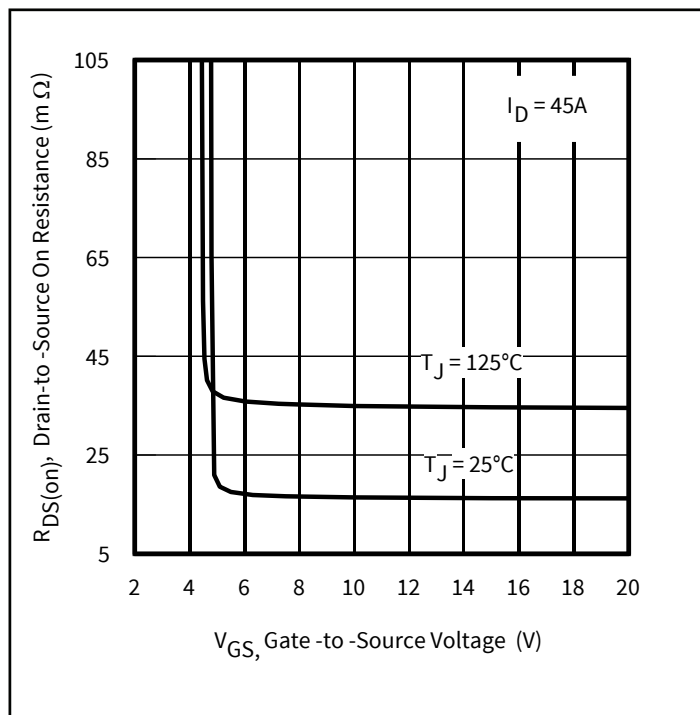


Figure 1 Typical On-Resistance vs. Gate Voltage

Figure 2 Maximum Drain Current vs. Case Temperature

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3 Electrical characteristics5

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1 Parameters

Table1 Key performance parameters

| Parameter | Values | Units |
|-------------------|--------|------------|
| V_{DS} | 300 | V |
| $R_{DS(on) \max}$ | 19 | m Ω |
| I_D | 75 | A |

2 Maximum ratings and thermal characteristics

Table 2 Maximum ratings (at $T_J=25^\circ\text{C}$, unless otherwise specified)

| Parameter | Symbol | Conditions | Values | Unit |
|---|--------------------|--|---------------------|------|
| Continuous Drain Current | I_D | $T_C = 25^\circ\text{C}$, $V_{GS} @ 10\text{V}$ | 75 | A |
| Continuous Drain Current | I_D | $T_C = 100^\circ\text{C}$, $V_{GS} @ 10\text{V}$ | 53 | |
| Pulsed Drain Current ① | I_{DM} | $T_C = 25^\circ\text{C}$ | 300 | |
| Maximum Power Dissipation | P_D | $T_C = 25^\circ\text{C}$ | 313 | W |
| Linear Derating Factor | | $T_C = 25^\circ\text{C}$ | 2.1 | W/°C |
| Peak Diode Recovery ③ | dv/dt | $T_J = 175^\circ\text{C}$, $I_S = 22\text{A}$, $V_{DS} = 150\text{V}$ | 6.0 | V/ns |
| Gate-to-Source Voltage | V_{GS} | - | ± 20 | V |
| Operating Junction and Storage Temperature Range | T_J T_{STG} | - | -55 to +175 | °C |
| Soldering Temperature, for 10 seconds (1.6mm from case) | - | - | 300 | |
| Mounting Torque, 6-32 or M3 Screw | - | - | 10 lbf·in (1.1 N·m) | - |

Table 3 Thermal characteristics

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|------------------------------------|-----------------|--|------|------|------|------|
| Junction-to-Case ⑦ | $R_{\theta JC}$ | T_J approximately 90°C | - | - | 0.48 | °C/W |
| Case-to-Sink, Flat Greased Surface | $R_{\theta CS}$ | - | - | 0.24 | - | |
| Junction-to-Ambient | $R_{\theta JA}$ | - | - | - | 40 | |

Table 4 Avalanche characteristics

| Parameter | Symbol | Values | Unit |
|---------------------------------|------------------------------|--------------------------|------|
| Single Pulse Avalanche Energy ② | E_{AS} (Thermally limited) | 459 | mJ |
| Avalanche Current ① | I_{AR} | See Fig 16, 17, 23a, 23b | A |
| Repetitive Avalanche Energy ① | E_{AR} | | mJ |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 1\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 30\text{A}$, $V_{GS} = 10\text{V}$.
- ③ $I_{SD} \leq 22\text{A}$, $di/dt \leq 1000\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ R_θ is measured at T_J approximately 90°C .

3 Electrical characteristics

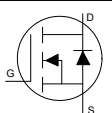
Table 5 Static characteristics

| Parameter | Symbol | Conditions | Values | | | Unit |
|--------------------------------------|---------------------------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 1mA$ | 300 | - | - | V |
| Breakdown Voltage Temp. Coefficient | $\Delta V_{(BR)DSS}/\Delta T_J$ | Reference to 25°C, $I_D = 2.5mA$ ① | - | 0.12 | - | V/°C |
| Static Drain-to-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 45A$ | - | 16 | 19 | mΩ |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 270\mu A$ | 2.0 | - | 4.0 | V |
| Drain-to-Source Leakage Current | I_{DSS} | $V_{DS} = 240V, V_{GS} = 0V$ | - | - | 10 | μA |
| | | $V_{DS} = 240V, V_{GS} = 0V, T_J = 125^\circ C$ | - | - | 300 | |
| Gate-to-Source Forward Leakage | I_{GSS} | $V_{GS} = 20V$ | - | - | 200 | nA |
| Gate Resistance | R_G | | - | 1.3 | - | Ω |

Table 6 Dynamic characteristics

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|---------------------|--|--------|-------|------|------|
| | | | Min. | Typ. | Max. | |
| Forward Trans conductance | gfs | $V_{DS} = 50V, I_D = 45A$ | 97 | - | - | S |
| Total Gate Charge | Q_g | $I_D = 45A$ $V_{DS} = 150V$ $V_{GS} = 10V$ | - | 127 | 191 | nC |
| Gate-to-Source Charge | Q_{gs} | | - | 44 | - | |
| Gate-to-Drain Charge | Q_{gd} | | - | 24 | - | |
| Total Gate Charge Sync. ($Q_g - Q_{gd}$) | Q_{sync} | | - | 103 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 150V$ | - | 25 | - | ns |
| Rise Time | t_r | $I_D = 45A$ | - | 44 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | $R_G = 2.7\Omega$ | - | 79 | - | |
| Fall Time | t_f | $V_{GS} = 10V$ | - | 32 | - | |
| Input Capacitance | C_{iss} | $V_{GS} = 0V$ | - | 10030 | - | pF |
| Output Capacitance | C_{oss} | $V_{DS} = 50V$ | - | 863 | - | |
| Reverse Transfer Capacitance | C_{rss} | $f = 1.0MHz$, See Fig.7 | - | 3.8 | - | |
| Effective Output Capacitance (Energy Related) | $C_{oss\ eff.(ER)}$ | $V_{GS} = 0V, V_{DS} = 0V$ to 240V ⑥ | - | 552 | - | |
| Output Capacitance (Time Related) | $C_{oss\ eff.(TR)}$ | $V_{GS} = 0V, V_{DS} = 0V$ to 240V ⑤ | - | 961 | - | |

Table 7 Reverse Diode

| Parameter | Symbol | Conditions | Values | | | Unit |
|--|-----------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Continuous Source Current (Body Diode) | I_S | MOSFET symbol showing the integral reverse p-n junction diode.  | - | - | 75 | A |
| Pulsed Source Current (Body Diode) ① | I_{SM} | | - | - | 300 | |
| Diode Forward Voltage | V_{SD} | $T_J = 25^\circ C, I_S = 45A, V_{GS} = 0V$ ④ | - | - | 1.2 | V |
| Reverse Recovery Time | t_{rr} | $T_J = 25^\circ C$ | - | 156 | - | ns |
| | | $T_J = 125^\circ C$ | - | 215 | - | |
| Reverse Recovery Charge | Q_{rr} | $T_J = 25^\circ C$ | - | 521 | - | nC |
| | | $T_J = 125^\circ C$ | - | 1145 | - | |
| Reverse Recovery Current | I_{RRM} | $T_J = 25^\circ C$ | - | 5.0 | - | A |
| | | $T_J = 125^\circ C$ | - | 7.8 | - | |

4 Electrical characteristic diagrams

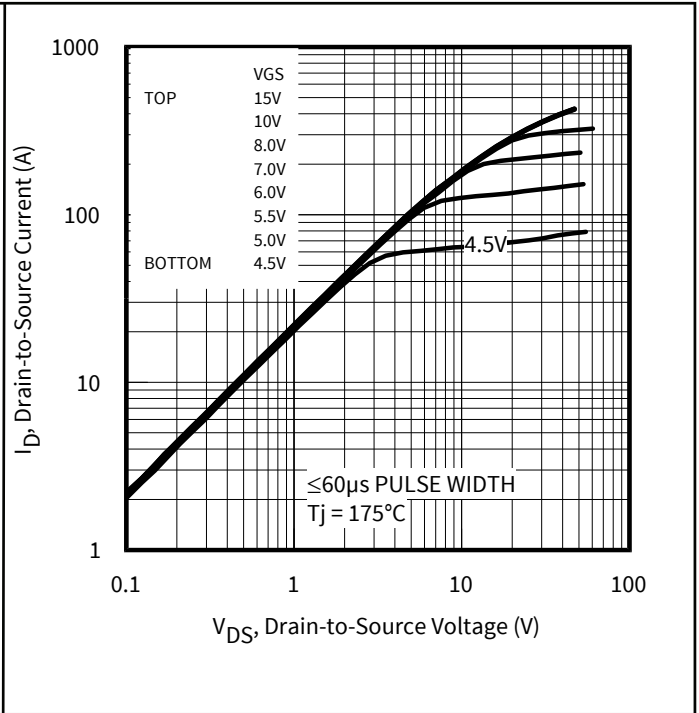
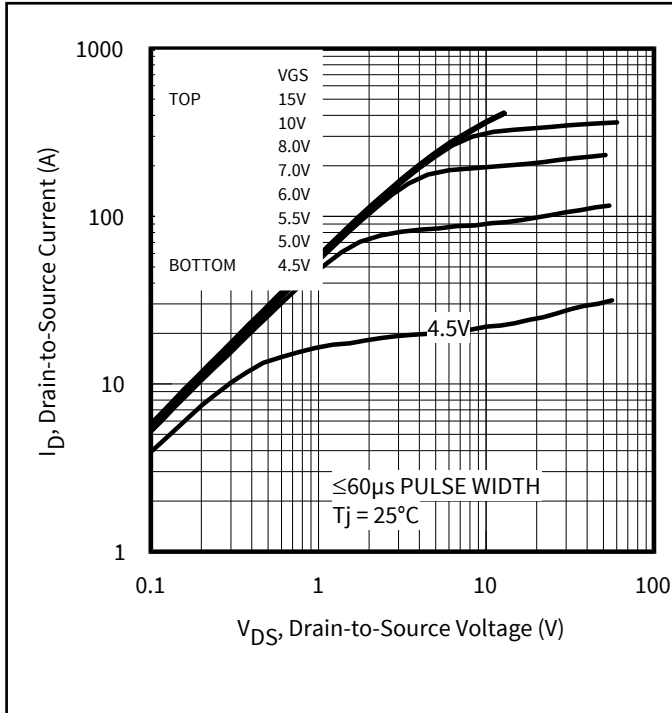


Figure 3 Typical Output Characteristics

Figure 4 Typical Output Characteristics

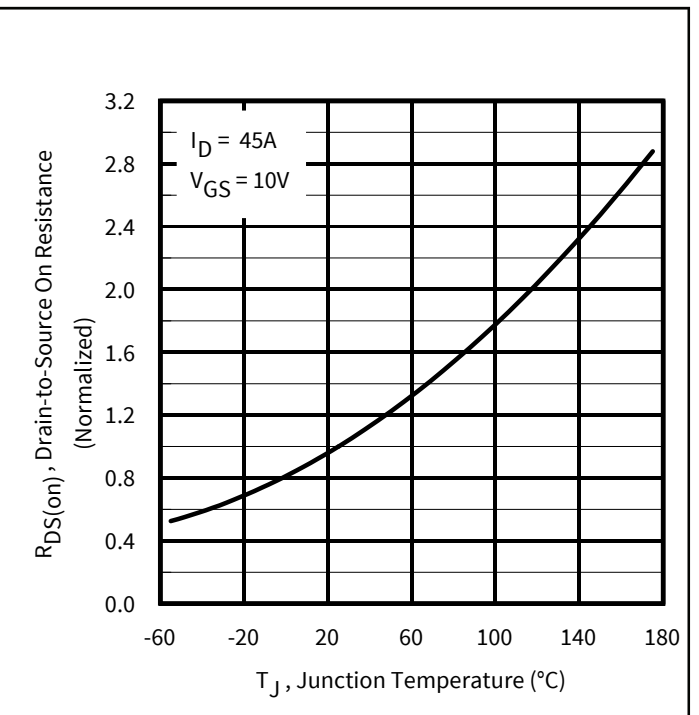
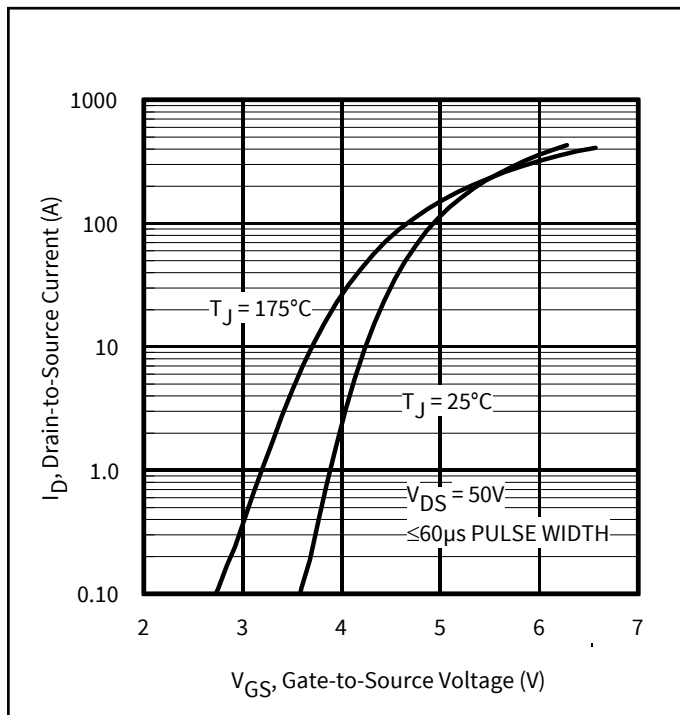


Figure 5 Typical Transfer Characteristics

Figure 6 Normalized On-Resistance vs. Temperature

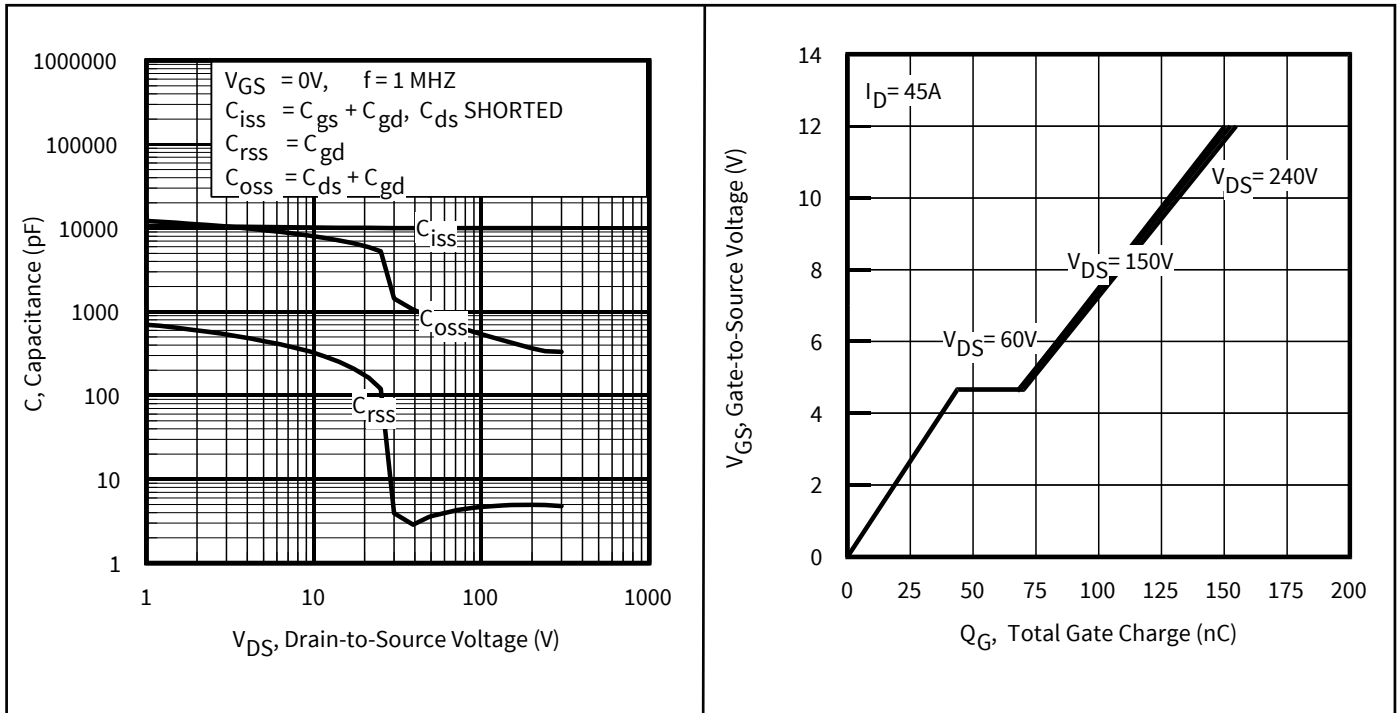


Figure 7 Typical Capacitance vs. Drain-to-Source Voltage

Figure 8 Typical Gate Charge vs. Gate-to-Source Voltage

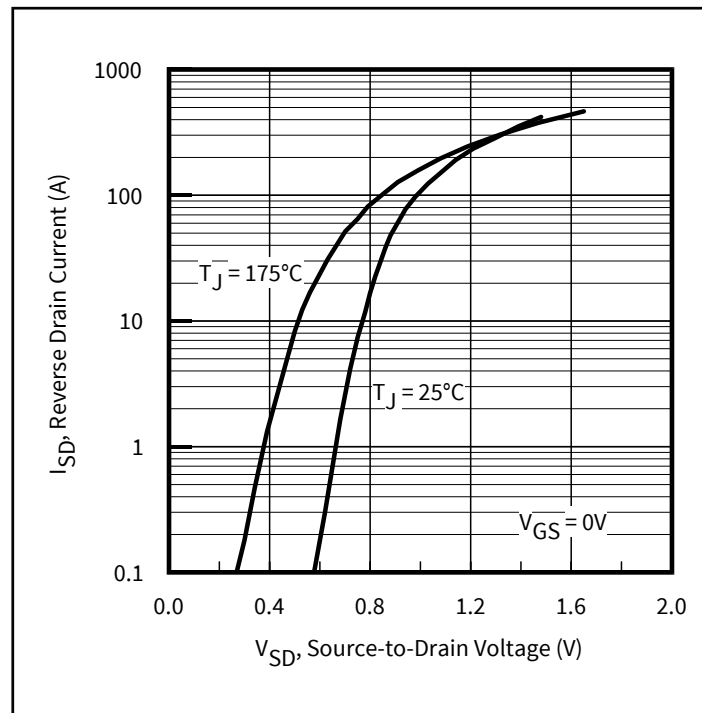


Figure 9 Typical Source-Drain Diode Forward Voltage

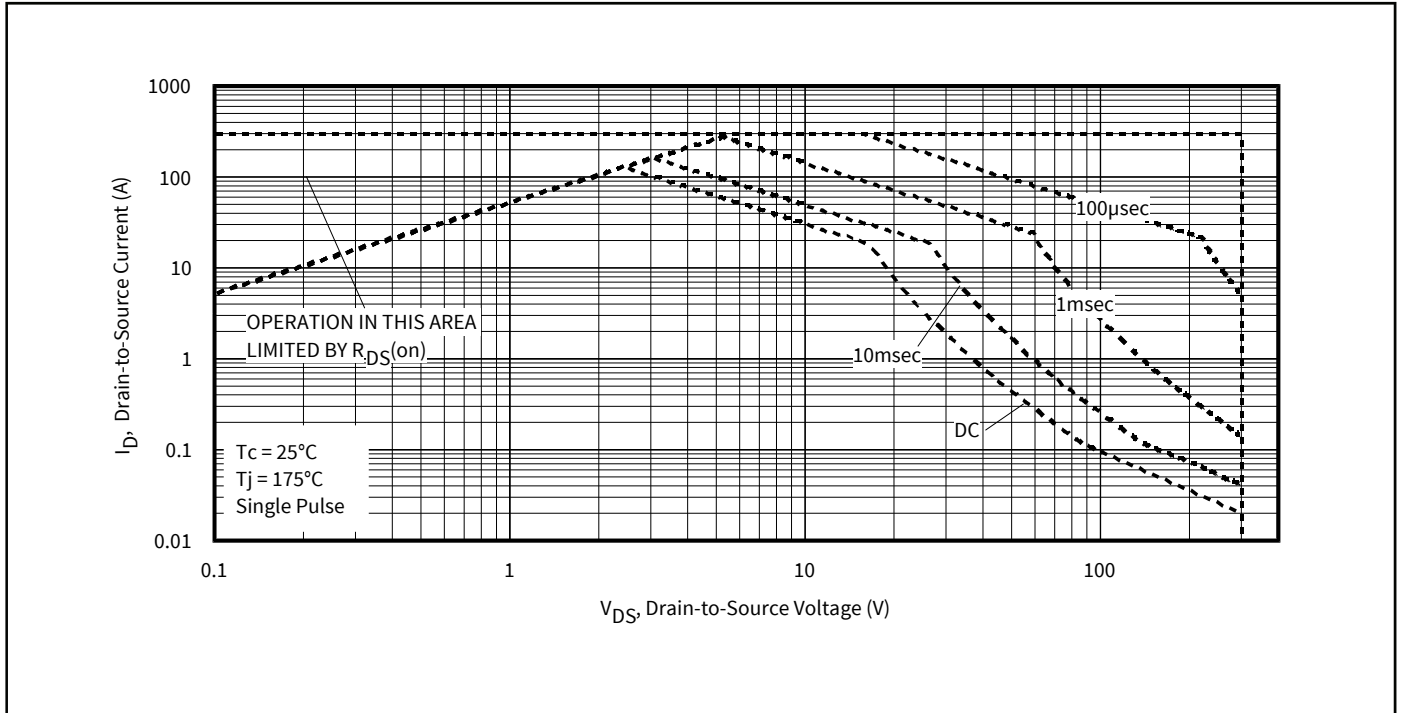


Figure 10 Maximum Safe Operating Area

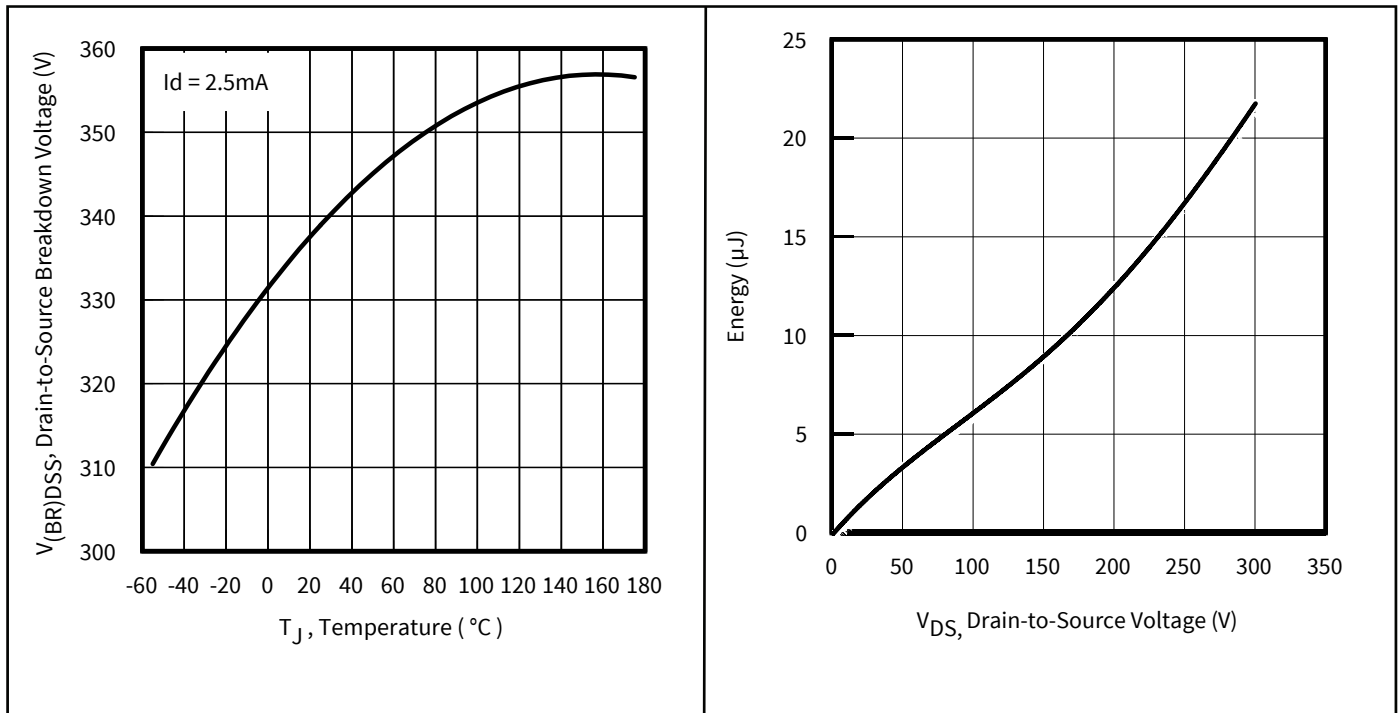


Figure 11 Drain-to-Source Breakdown Voltage

Figure 12 Typical Coss Stored Energy

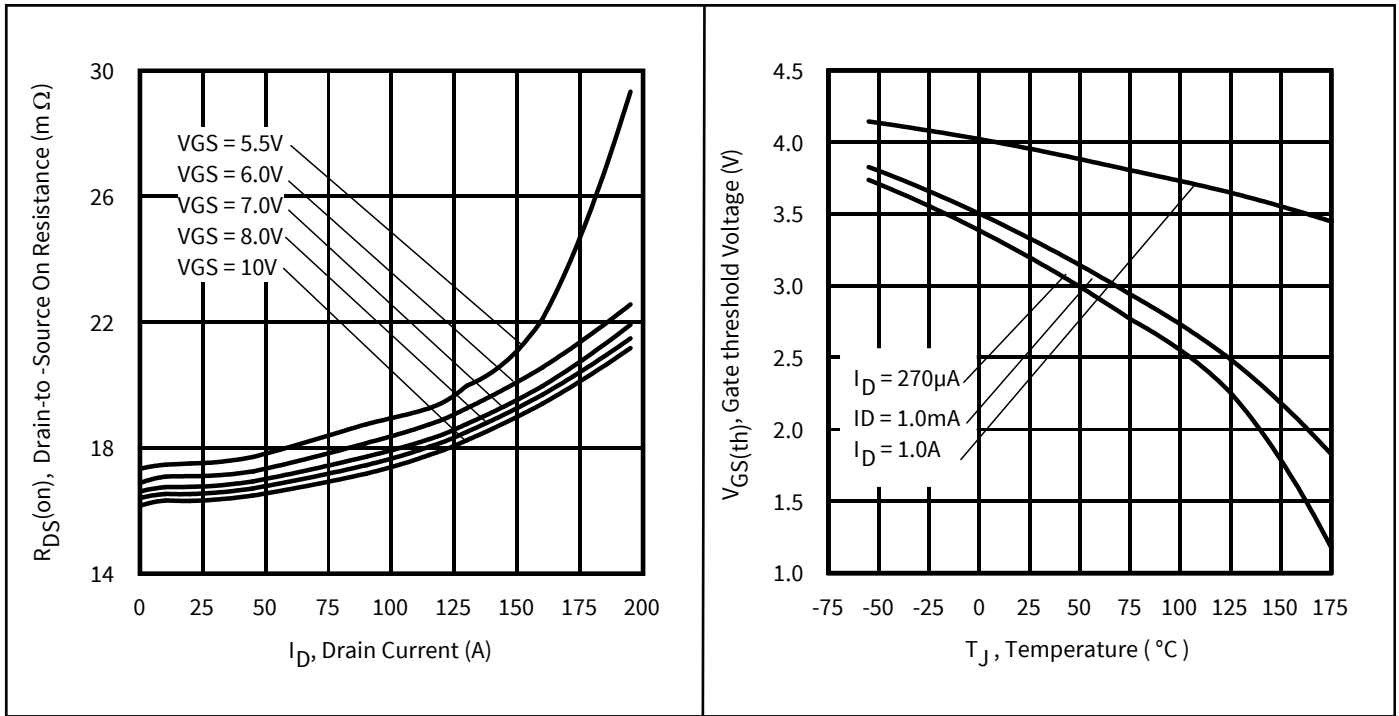


Figure 13 Typical On-Resistance vs. Drain Current

Figure 14 Threshold Voltage vs. Temperature

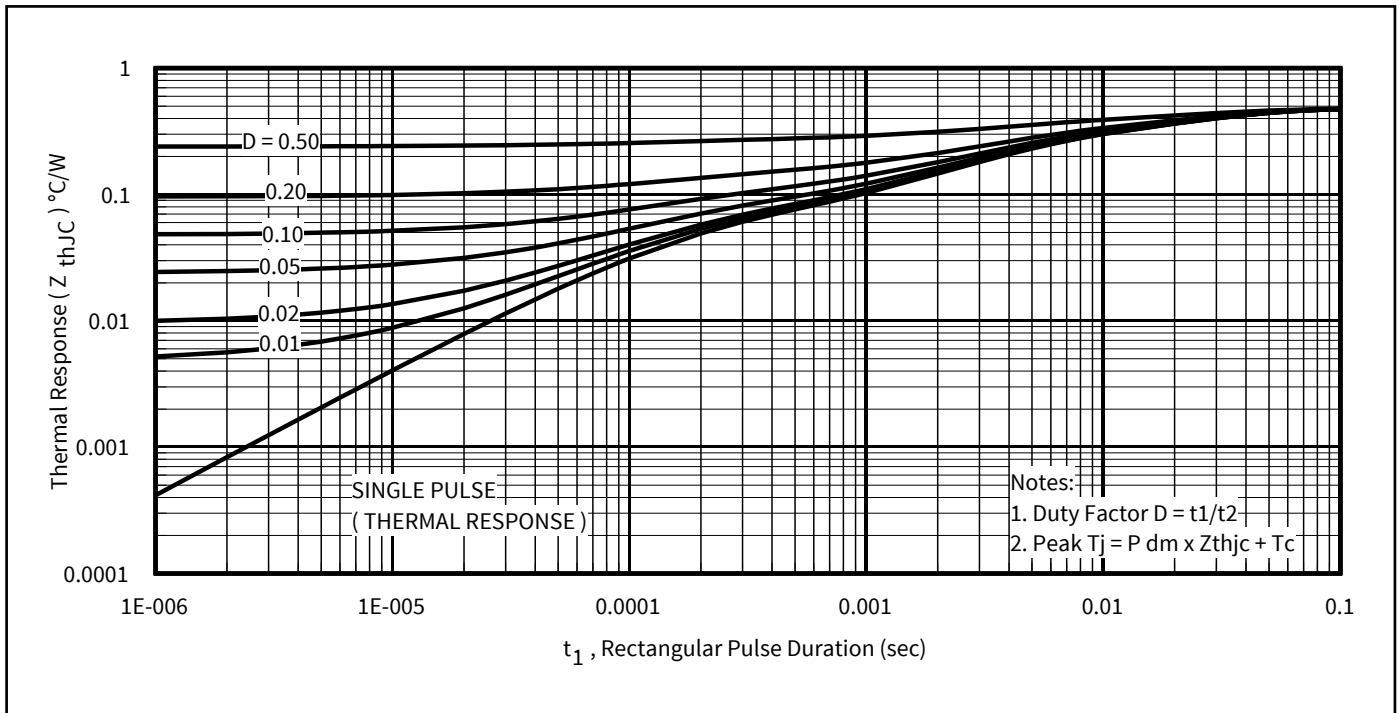


Figure 15 Maximum Effective Transient Thermal Impedance, Junction-to-Case

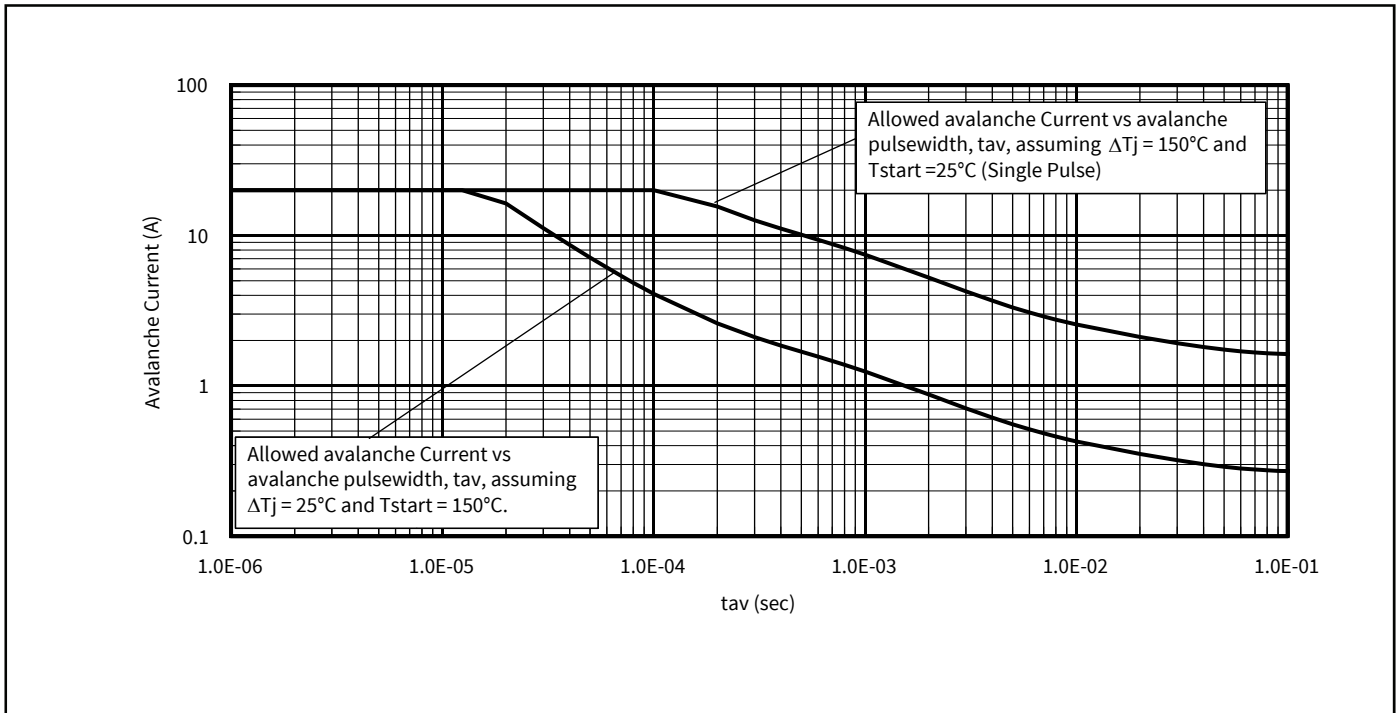
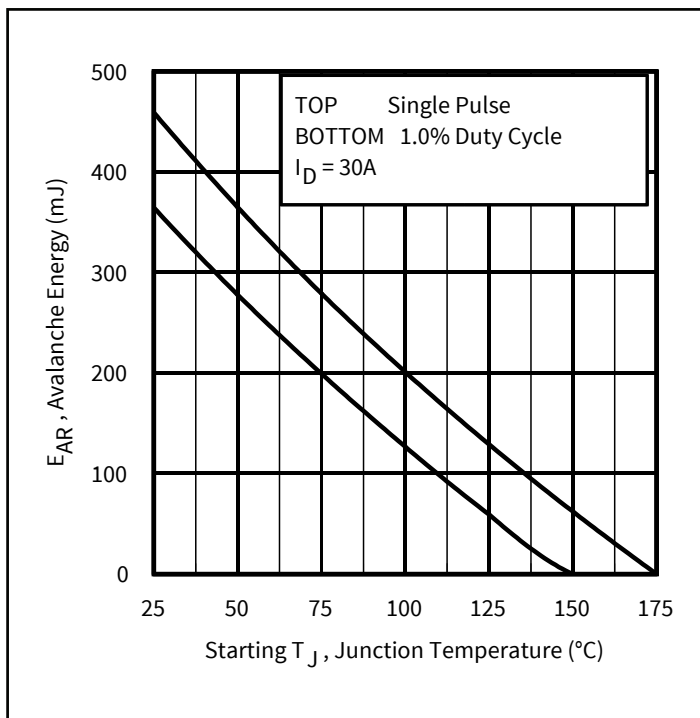


Figure 16 Avalanche Current vs. Pulse Width



Notes on Repetitive Avalanche Curves, Figures 16, 17:
 (For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
 Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 14)
 $P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$

Figure 17 Maximum Avalanche Energy vs. Temperature

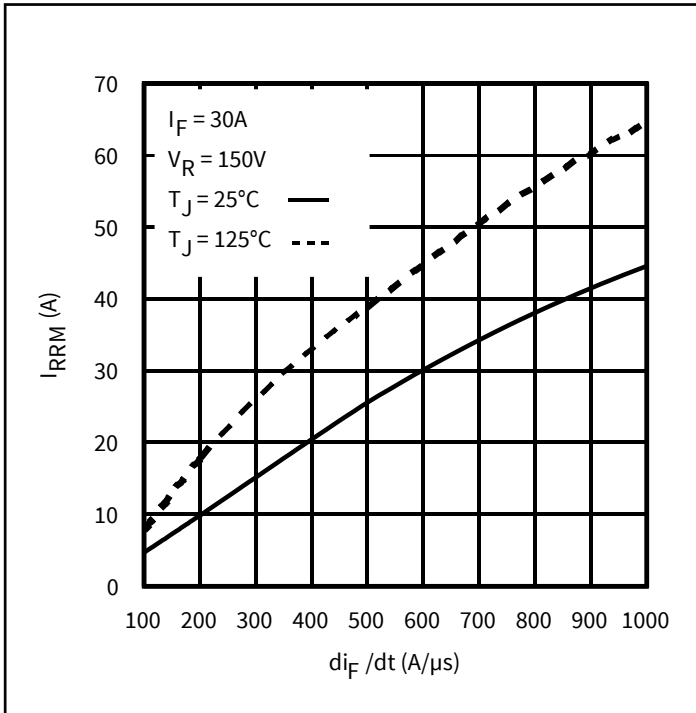


Figure 18 Typical Recovery Current vs. di_F/dt

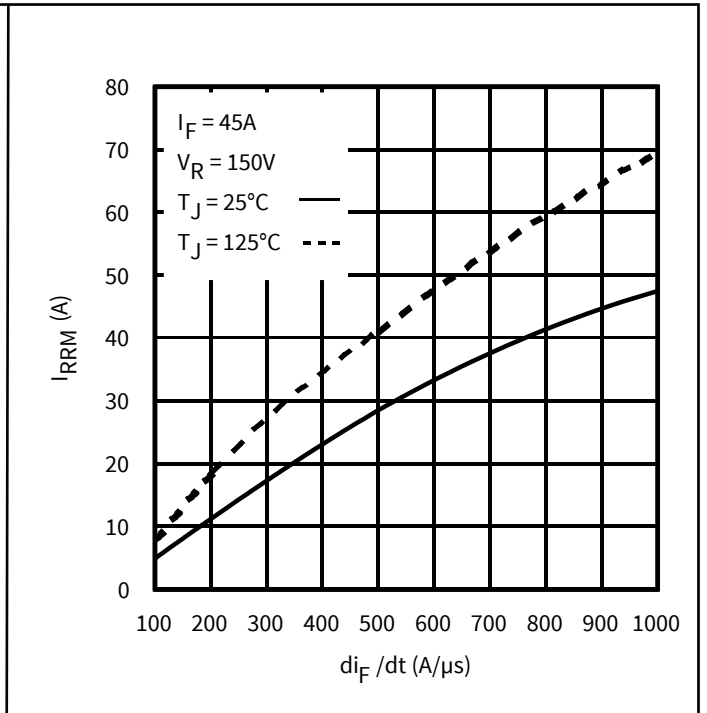


Figure 19 Typical Recovery Current vs. di_F/dt

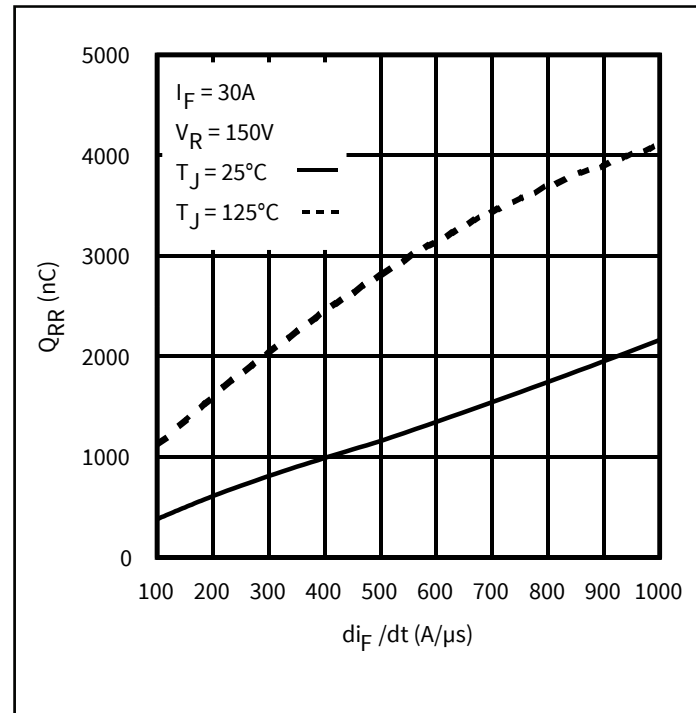


Figure 20 Typical Stored Charge vs. di_F/dt

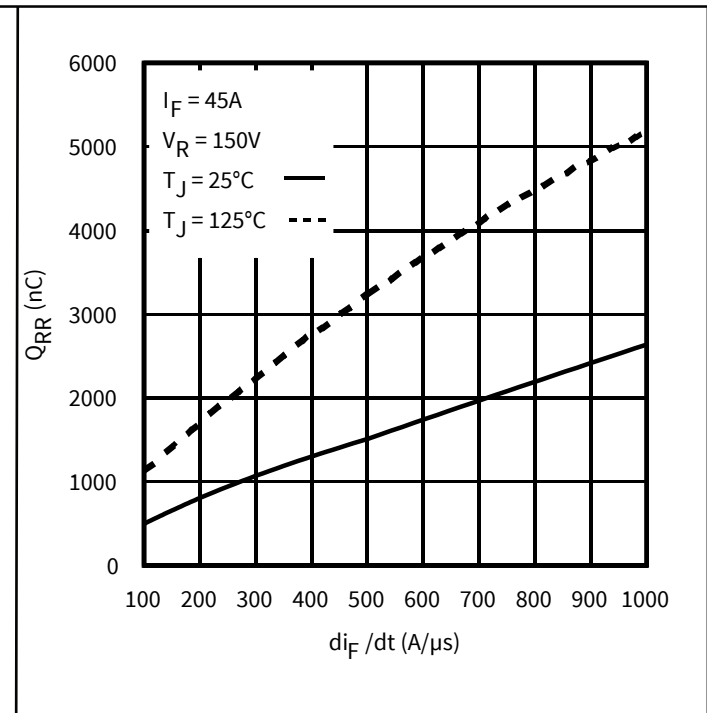


Figure 21 Typical Stored Charge vs. di_F/dt

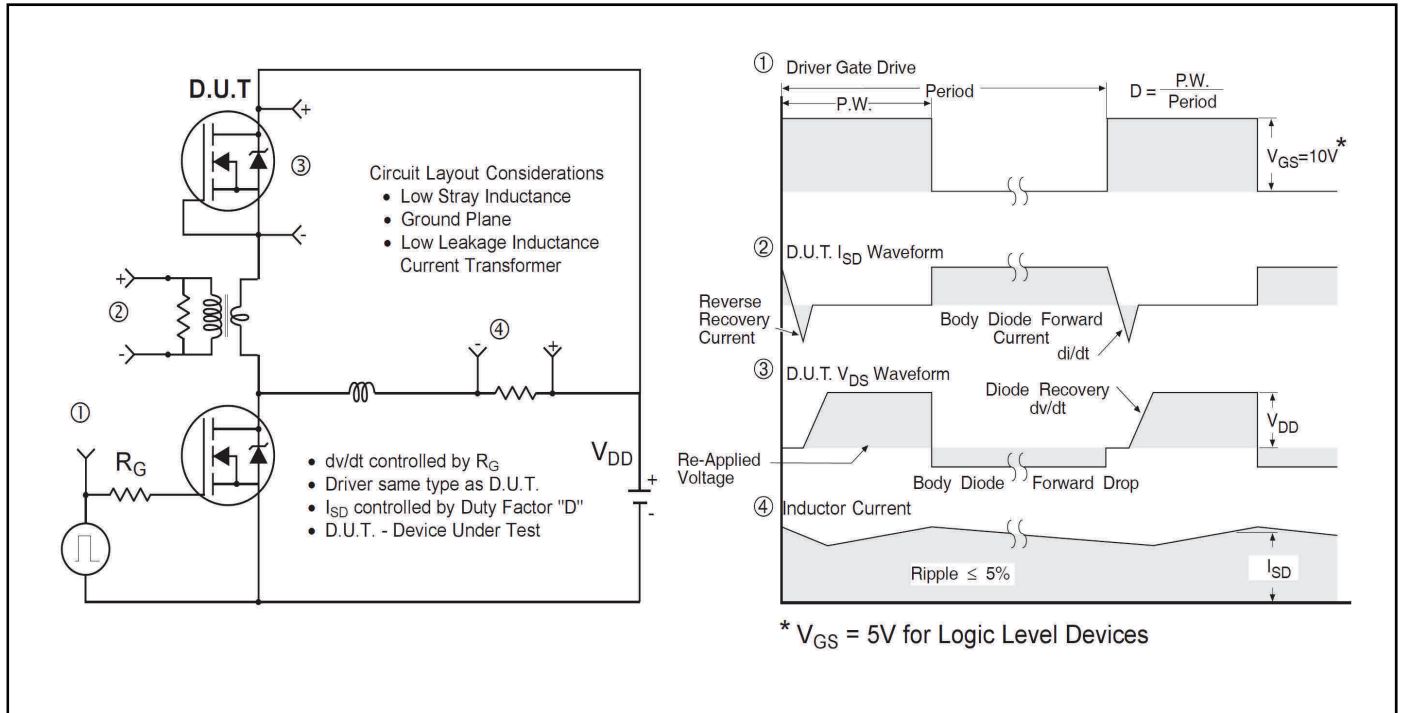


Figure 22 Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET™ Power MOSFETs

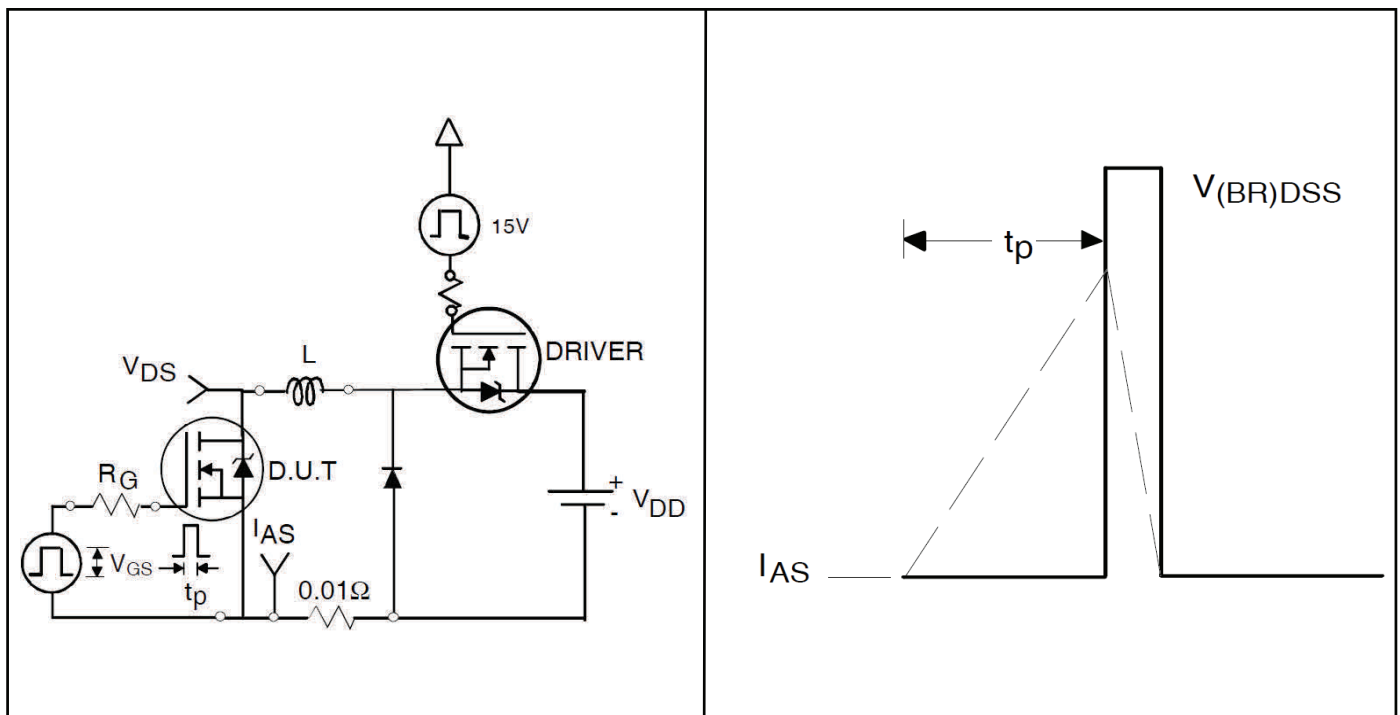


Figure 23a Unclamped Inductive Test Circuit

Figure 23b Unclamped Inductive Waveforms

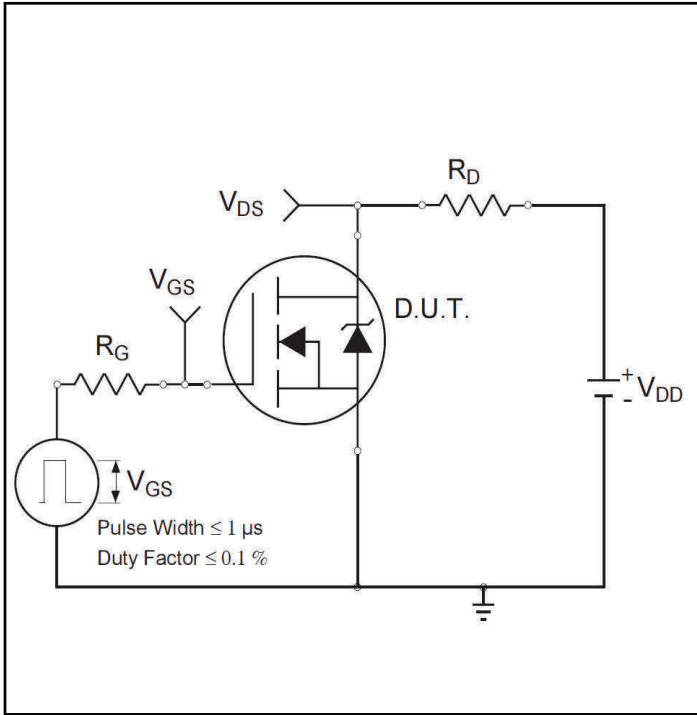


Figure 24a Switching Time Test Circuit

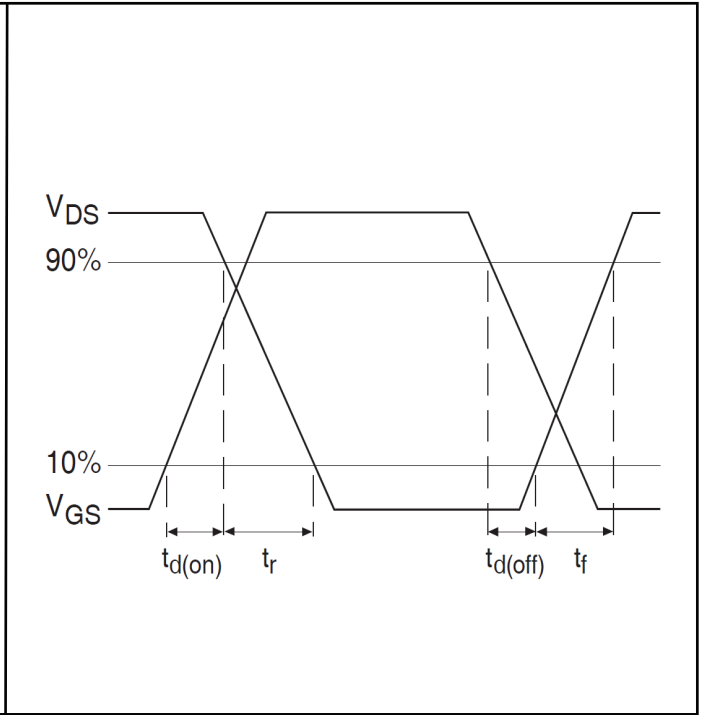


Figure 24b Switching Time Waveforms

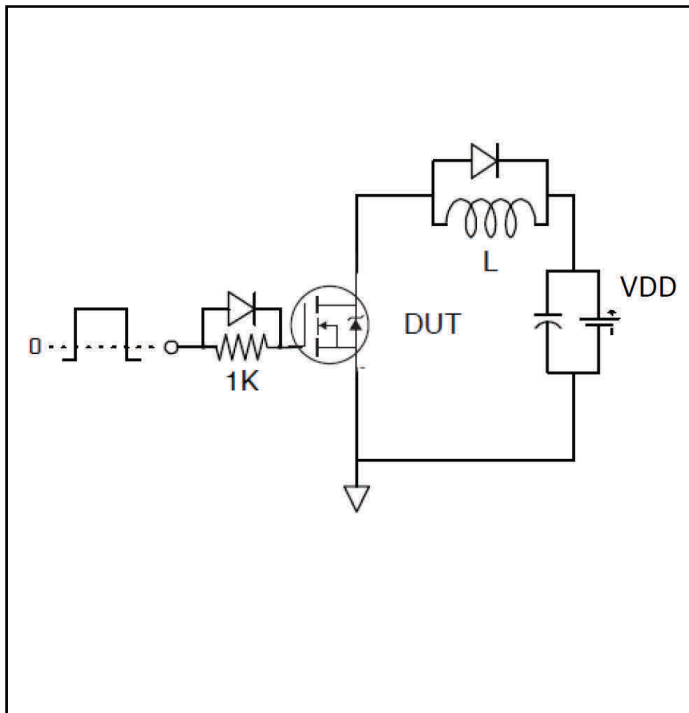


Figure 25a Gate Charge Test Circuit

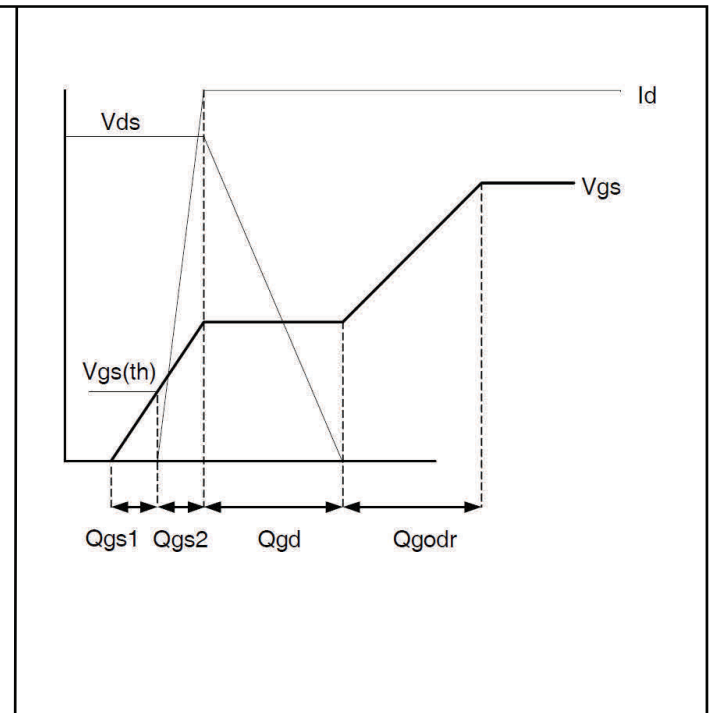
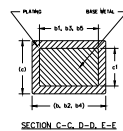
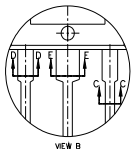
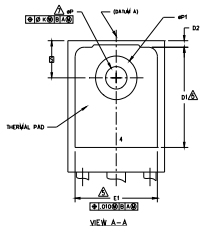
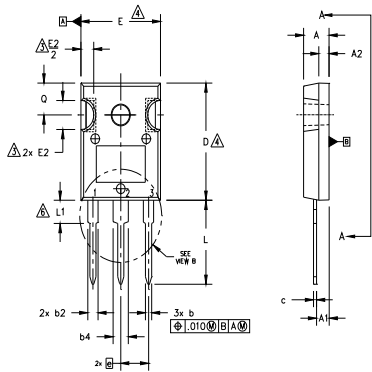


Figure 25b Gate Charge Waveform

5 Package Information

TO-247AC Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ϕP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

| SYMBOL | DIMENSIONS | | | | NOTES |
|-----------|------------|------|-------------|-------|-------|
| | INCHES | | MILLIMETERS | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | .183 | .209 | 4.65 | 5.31 | |
| A1 | .087 | .102 | 2.21 | 2.59 | |
| A2 | .059 | .098 | 1.50 | 2.49 | |
| b | .039 | .055 | 0.99 | 1.40 | |
| b1 | .039 | .053 | 0.99 | 1.35 | |
| b2 | .065 | .094 | 1.65 | 2.39 | |
| b3 | .065 | .092 | 1.65 | 2.34 | |
| b4 | .102 | .135 | 2.59 | 3.43 | |
| b5 | .102 | .133 | 2.59 | 3.38 | |
| c | .015 | .035 | 0.38 | 0.89 | |
| c1 | .015 | .033 | 0.38 | 0.84 | |
| D | .776 | .815 | 19.71 | 20.70 | 4 |
| D1 | .515 | - | 13.08 | - | 5 |
| D2 | .020 | .053 | 0.51 | 1.35 | |
| E | .602 | .625 | 15.29 | 15.87 | 4 |
| E1 | .530 | - | 13.46 | - | |
| E2 | .178 | .216 | 4.52 | 5.49 | |
| e | .215 BSC | | 5.46 BSC | | |
| ϕk | .010 | | 0.25 | | |
| L | .559 | .634 | 14.20 | 16.10 | |
| L1 | .146 | .169 | 3.71 | 4.29 | |
| ϕP | .140 | .144 | 3.56 | 3.66 | |
| $\phi P1$ | - | .291 | - | 7.39 | |
| Q | .209 | .224 | 5.31 | 5.69 | |
| S | .217 BSC | | 5.51 BSC | | |

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

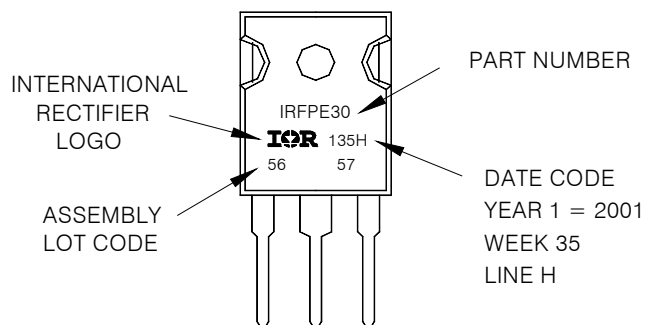
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

6 Qualification Information

Qualification Information

| | | |
|-----------------------------------|-------------------------------------|-----|
| Qualification Level | Industrial (per JEDEC JESD47F) † | |
| Moisture Sensitivity Level | TO-247AC | N/A |
| RoHS Compliant | Yes | |

† Applicable version of JEDEC standard at the time of product release.

Revision History**Major changes since the last revision**

| Page or Reference | Revision | Date | Description of changes |
|--------------------------|-----------------|-------------|---|
| All pages | 2.0 | 2017-11-14 | <ul style="list-style-type: none">• First release data sheet. |

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Email: erratum@infineon.com

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